# INTERNATIONAL STANDARD

# IEC 60747-4-2

QC 750116 First edition 2000-04

Semiconductor devices - Discrete devices -

# Part 4-2:

Microwave diodes and transistors – Integrated-circuit microwave amplifiers – Blank detail specification

Dispositifs à sernicanducteurs - Dispositifs discrets -

Partie 4-2;

Diodes et transistors hyperfréquences – Amplificateurs hyperfréquences pour circuits intégrés – Spécification particulière-cadre



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- IEC Bulletin
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#### Terminology, graphical and letter symbols

For general terminology, readers are referred to IEC 60050: International Electrotechnical Vocabulary (EV).

For graphical symbols, and letter symbols and signs approved by the IEC for general use, readers are referred to publications IEC 60027: Letter symbols to be used in electrical technology, IEC 60417: Graphical symbols for use on equipment. Index, survey and compilation of the single sheets and IEC 60617: Graphical symbols for diagrams.

Se web site address on title page.

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International Electrotechnical Commission 3, rue de Varembé Geneva, Switzerland Telefax: +41 22 919 0300 e-mail: inmail@iec.ch IEC web site http://www.iec.ch



Commission Electrotechnique Internationale International Electrotechnical Commission Международная Электротехническая Комиссия

PRICE CODE



### INTERNATIONAL ELECTROTECHNICAL COMMISSION

#### SEMICONDUCTOR DEVICES - DISCRETE DEVICES -

# Part 4-2: Microwave diodes and transistors – Integrated-circuit microwave amplifiers – Blank detail specification

### **FOREWORD**

- 1) The IEC (International Electrotechnical Commission) is a worldwide organization for standardization comprising all national electrotechnical committees (IEC National Committees). The object of the IEC is to promote international cooperation on all questions concerning standardization in the electrical and electronic fields. To this end and in addition to other activities, the IEC publishes International Standards. Their preparation is entrusted to technical committees; any IEC National Committee interested in the subject dealt with may participate in this preparatory work. International, governmental and non-governmental organizations liaising with the IEC also participate in this preparation. The IEC collaborates closely with the International Organization for Standardization (ISO) in accordance with conditions determined by agreement between the two organizations.
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- 3) The documents produced have the form of recommendations for international use and are published in the form of standards, technical specifications, technical reports or guides and they are accepted by the National Committees in that sense.
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- 6) Attention is drawn to the possibility that some of the elements of this International Standard may be the subject of patent rights. The IEC shall not be held responsible for dentifying any or all such patent rights.

International Standard NEC 60747-4-2 has been prepared by subcommittee 47E: Discrete semiconductor devices, of IEC technical committee 47: Semiconductor devices.

This standard is a blank detail specification for integrated-circuit microwave amplifiers.

The text of this standard is based on the following documents:

FDIS	Report on voting
47E/142/FDIS	47E/148/RVD

Full information on the voting for the approval of this standard can be found in the report on voting indicated in the above table.

This publication has not been drafted in complete accordance with the ISO/IEC Directives, Part 3.

The QC number that appears on the front cover of this publication is the specification number in the IEC Quality Assessment System for Electronic Components (IECQ).

A bilingual version of this standard may be issued at a later date.

The committee has decided that the contents of this publication will remain unchanged until 2005. At this date, the publication will be

- · reconfirmed;
- withdrawn;
- replaced by a revised edition, or
- amended.

Other IEC publications quoted in this standard:

Publication Nos.

IEC 60068-2-17:1994, Basic environmental testing procedures – Part 2: Tests – Test Q: Sealing

IEC 60747-1:1983, Semiconductor devices – Discrete devices – Part 1: General

IEC 60747-4:1991, Semiconductor devices – Discrete devices – Part 4: Microwave diodes and transistors

IEC 60747-10:1991, Semiconductor devices – Part 10: Generic specification for discrete devices and integrated circuits

IEC 60748-1:1984, Semiconductor devices - Integrated circuits - Part 1: General

IEC 60748-11:1990, Semiconductor devices - Integrated circuits - Part 11: Sectional specification for semiconductor integrated circuit excluding hybrid circuits

IEC 60749:1996, Semiconductor devices - Mechanical and climatic test methods

IEC QC 001002:1986, Rules of Procedure of the IEC Quality Assessment System for Electronic Components (IECQ)

#### SEMICONDUCTOR DEVICES - DISCRETE DEVICES -

# Part 4-2: Microwave diodes and transistors – Integrated-circuit microwave amplifiers – Blank detail specification

#### INTRODUCTION

The IEC Quality Assessment System for Electronic Components is operated in accordance with the statutes of the IEC and under the authority of the IEC. The object of this system is to define quality assessment procedures in such a manner that electronic components released by one participating country as conforming with the requirements of an applicable specification are equally acceptable in all other participating countries without the need for further testing.

This blank detail specification is one of a series of blank detail specifications for semiconductor devices and shall be used with the following IEC publications:

IEC 60747-10/QC 700000:1991, Semiconductor devices Part 10 Generic specification for discrete devices and integrated circuits

IEC 60748-11/QC 790100:1990, Semiconductor devices - Integrated circuits - Part 11: Sectional specification for semiconductor integrated circuits excluding hybrid circuits

#### Required information

Numbers shown in brackets on this and the following pages correspond to the following items of required information, which should be entered in the spaces provided.

Identification of the detail specification

- [1] The name of the national standards organization under whose authority the detail specification is issued.
- [2] The IECQ number of the detail specification.
- [3] The numbers and issue numbers of the generic and sectional specifications.
- [4] The national number of the detail specification, date of issue and any further information required by the national system.

# Identification of the component

- [5] Main function and type number.
- [6] Information on typical construction (materials, main technology) and package. If the device has several kinds of derivative products, these differences shall be indicated, for example features in the comparison table.
  - For electrostatic sensitive devices, a note of caution regarding electrostatic sensitivity shall be added in the detail specification.
- [7] Outline drawing, terminal identification, marking and/or reference to the relevant document for outlines.
- [8] Category of assessed quality according to 2.6 of the generic specification.
- [9] Reference data.

[Throughout this standard, the texts given in square brackets are intended to serve as guidance for the specification writer and shall not be included in the detail specification.]

[When confusion may arise as to whether a paragraph is meant as an instruction to the writer or not, it shall be given in brackets.]

[Name (address) of responsible NAI [ and possibly of the body from which the specification is available.)	[2] [Number of IECQ detail specification, plus issue number and/or date.] QC 750116
ELECTRONIC COMPONENT OF ASSESSED [3 QUALITY IN ACCORDANCE WITH:	National number of detail specification [4]
Generic specification: 60747-10/QC 700000	[This box need not be used if national number
Sectional specification: 60748-11/QC 790100	repeats IECQ number.]
[and national references if different.]	
BLANK DETAIL SPECIFICATION FOR: INTEGR	ATED-CIRCUIT MICROWAVE AMPLIFIERS [5]
Type number(s) of the relevant device(s).] Ordering information: see 1.2 of this standard.	
Mechanical description [	7] Short description [6]
Outline references: [Standard package reference should be given, IEC number (mandatory, if available) and/or national number.]  Outline drawing: [May be transferred to or given with more details in clause 8 of this standard.]  Terminal identification: [Drawing showing pin assignments, including with more details in clause showing pin assignments, including with more details in clause showing pin assignments, including with more details.	Monolithic microwave-integrated circuits  Semiconductor material: [GaAs, Si]  Encapsulation: [cavity or non-cavity].  Application(s) see clause 5 of this standard.  Caution: observe precautions for handling  ELECTROSTATIC-SENSITIVE DEVICES  [if applicable]
Marking: [Letters and figures, or color code.] [The detail specification shall prescribe the information to be marked on the device, if any.] [See 2.5 of the generic specification and/or 1.1 of this standard.]	
/ frh.	Reference data [9]
(FCKIR)	[Reference data on the most important properties to permit comparison between component types.]
Information about manufacturers who have compavailable in the current Qualified Products List.	onents qualified to this detail specification is

# 1 Marking and ordering information

#### 1.1 Marking

[See 2.5 of generic specification.

The detail specification shall state the information marked for the relevant types, such as letters, figures and/or codes.

When the marking contains items other than those specified in 2.5 of the generic specification, such as used for the manufacturer's internal use, this should be indicated.

If all the information has already appeared in box [7] on the front page, this shall be indicated.]

# 1.2 Ordering information

[The following minimum information is necessary to order a specific device, unless otherwise specified:

- precise type reference (and nominal voltage value, if required);
- IECQ reference of detail specification with issue pumber and/or date when relevant;
- category of assessed quality as defined in clause 9 of the sectional specification and, if required, screening sequence as defined in clause 8 of the same.
- packaging for delivery;
- any other particulars.]

# 2 Application-related description

[Information regarding application in equipments or in circuits, and the relation with the associated devices shall be given here. See (EC 60748-1, Chapter VI.]

# 3 Specification of the function

[Information regarding the function of the device shall be given here. Items to be given here shall be selected from IEO 60748-1, Chapter VI.]

# 4 Limiting values (absolute maximum rating system)

These values apply over the operating temperature range, unless otherwise specified.

[Repeat only subclause numbers used, together with title. Any additional values shall be given at the appropriate place, but without subclause number.]

[Curves shall preferably be given in clause 9 of the detail specification.]

Categories Type A: low-noise

Type B: auto-gain control

Type C: limiting Type D: power

Subclause	Limiting value	Symbol	Type A		Тур	е В	Туре С		е С Туре	
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.
4.1	Ambient or case temperature	T <sub>amb</sub> or T <sub>case</sub>	×	×	×	×	×	×	×	×
4.2	Storage temperature	$ au_{stg}$	×	×	×	×	×	×	×	×
4.3	Power supply voltage(s) [note 1]	$V_{xxi}$		×		×		×		×
4.4	Power supply current(s) [note 1]	$I_{xxi}$		×		×		2×2	)	×
4.5	Terminal voltage(s) [notes 1 and 2]	$V_{xxi}$		×		×	8			×
4.6	Terminal current(s) [notes 1 and 2]	$I_{xxi}$		×		T.	K.K.	\*\		×
4.7	Input power	$P_{in}$	/	/X/	K	//x/	$\langle \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$	×		×
4.8	Channel temperature	$T_{ch};\;T_{j}$		×	10	×		×		×
4.9	Power dissipation [note 3]	P <sub>tot</sub>	$\Omega$	, W	7	<b>&gt;</b>		×		×

NOTE 1 'xx' is the symbol of a terminal and 'i' is the terminal number of the same kind, such as  $V_{\rm GG1}$  for the voltage of the first gate terminal and  $I_{\rm DD2}$  for the current of the second drain terminal.

NOTE 2 Where appropriate.

NOTE 3 Maximum value over the specified range of operating ambient or reference-point temperatures. Any special requirements for ventilation and/or mounting shall be stated.

# 5 Operating conditions (within the specified operating ambient or case temperature range)

Operating conditions are specified in the relevant measuring methods.

See 13.2 of this standard for inspection requirements.

- 5.1 Power supply voltage
- 5.2 Power supply current
- **5.3 Input power** (where appropriate)
- 5.4 Voltage and/or current at another or other terminal(s) (where appropriate)
- **5.5** External element(s) (where appropriate)
- 5.6 Operating frequency range
- 5.7 Operating temperature range

#### 6 Electrical characteristics

[Repeat only subclause numbers used, with title. Any additional characteristics shall be given at the appropriate place but without subclause number.]

[When several devices are defined in the same detail specification, the relevant values shall be given on successive lines whilst avoiding the repetition of identical values.]

[Curves should preferably be given under clause 9 of the detail specification.]

The following characteristics apply over the full operating ambient temperature range, unless otherwise stated.

[Where the stated performance of the circuit varies over the operating ambient emperature range, the values of the appropriate characteristics shall be stated at 25 °C and at the extremes of the operating temperature range.]

#### 6.1 Static characteristics

Sub-			Symbol Type A		Туре В		Type C		Type D		Tested
clause	$T_{\rm amb}$ or $T_{\rm case}$ = 25 °C, unless otherwise specified (see clause 4 of the generic specification)		Mim.	Max.	Min	Max.	Min.	Max.	Min.	Max.	
6.1.1	Power supply current(s): value(s) at specified supply voltage(s)	/ <sub>xxi</sub>	×	(X)	×	×	×	×	×	×	А3
6.1.2	Thermal resistance channel to case: value at specified $T_{\text{case}}$	R <sub>th(j-c)</sub>			>			×		×	C2d

# 6.2 AC characteristics

Sub-	Characteristics and conditions at	Symbol	Тур	e A	Тур	е В	Тур	e C	Тур	e D	Tested
clause	$T_{\rm amb}$ or $T_{\rm case} = 25$ °C, unless otherwise specified (see clause 4) of the generic specification)		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
6.2.1	Linear gain: value at specified bias conditions and f	$G_{lin}$	×		×				×		A4
6.2.2	Linear gain flamess, value at specified bias conditions and specified frequency range	$\Delta G_{lin}$		×		×				×	A4
6.2.3	Power gain: value at specified bias conditions, $f$ and $P_{in}$	$G_{p}$			×				×		A4
6.2.4	Power gain flatness: value at specified bias conditions, specified frequency range and $P_{in}$	$\Delta G_{p}$				×				×	A4
6.2.5	Gain reduction: value at specified bias conditions, f and AGC bias	$\Delta G_{red}$			×						A4
6.2.6	Limiting output power: value at specified bias conditions, $f$ , $P_{\text{imin}}$ and $P_{\text{imax}}$	$P_{\rm o(ltg)}$					×	×			A4

# 6.2 (continued)

Sub-	Characteristics and conditions at	Symbol	Тур	e A	Тур	e B	Тур	e C	Тур	e D	Tested
clause	$T_{\rm amb}$ or $T_{\rm case}$ = 25 °C, unless otherwise specified (see clause 4 of the generic specification)		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
6.2.7	Limiting output power flatness: value at specified bias conditions, specified frequency range, $P_{\rm imin}$ and $P_{\rm imax}$	$\Delta P_{ m o(ltg)}$						×			A4
6.2.8	Output power: value at specified bias conditions, $f$ and $P_{in}$	$P_{\circ}$			×				×		A4
6.2.9	Output power at 1 dB-gain compression: value at specified bias conditions, <i>f</i>	P <sub>o(1dB)</sub>	×*		×				×	90	A4
6.2.10	Noise figure: value at specified bias conditions and <i>f</i>	F		×		(		N	2×		A4
6.2.11	Intermodulation distortion: value at specified bias conditions, $f$ and $P_{\rm in}$	P <sub>n</sub> /P <sub>1</sub>					W	XX	$\Diamond$	×	C2a
6.2.12	Power at the intercept point: value at specified bias conditions, $f$ and $P_{\rm in}$	$P_{n(IP)}$	×*					$\Diamond$	×		C2a
6.2.13	Magnitude of the input reflection coefficient (input return loss): value at specified bias conditions, $f$ and $P_{\rm in}$	\$11	×,		\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \		•		×		A4
6.2.14	Magnitude of the output reflection coefficient (output return loss): value at specified bias conditions, $f$ and $P_{\text{in}}$	IS28			>						A4
6.2.15	Magnitude of the reverse transmission coefficient (isolation): value at specified bias conditions, $f$ and $P_{\rm in}$	15/2/1			×		×		×		C2a
6.2.16	Conversion coefficient of amplitude modulation to phase modulation value at specified bias conditions, and $P_{\rm in}$	α(AM-PM)						×		×	C2a
6.2.17	Group delay time: value at specified bias conditions, rand Pi	$t_{ m d(grp)}$				×		×		×	C2a

NOTE For types B and D either the parameter set of 6.2.1, 6.2.2 and 6.2.8 or that of 6.2.3, 6.2.4 and 6.2.9 shall be selected.

# 7 Programming

Not applicable.

# 8 Mechanical and environmental ratings, characteristics and data

[Any specific mechanical and/or environmental ratings applicable shall be in accordance with IEC 60748-1, Chapter VI, 10.8 (see also IEC 60747-1, Chapter VI, clause 7).]

Where appropriate.

#### 9 Additional information

The information given here is not for inspection purposes.

The information given hereinafter may be seen to constitute minimum design data.

#### 9.1 Block diagram

[A block diagram, or equivalent circuit information, for the integrated circuit shall be given.]

#### 9.2 Recommendation for any associated device(s)

[Where required, any associated device(s), for example decoupling of power supply to high-frequency device, shall be given.]

## 9.3 Effects of temperature

[Variations of linear gain, power gain, output power, output power at 1 bb gain compression and noise figure in relation to temperature shall be given.]

### 9.4 Handling precautions, or electrostatic-sensitive device(s)

[Any limiting mechanical or environmental conditions shall be included, for example regarding the handling of high-power amplifiers.]

### 9.5 Internal protection

[A statement shall be given to indicate whether the integrated circuit contains internal protection against high static voltage or electrical fields.]

#### 9.6 Application data

# 10 Screening

[Where required, the blank detail specification shall make reference to clause 8 of the sectional specification and give any additional technical requirements.]

# 11 Quality assessment procedures

The blank detail specification shall specify whether the qualification approval procedure or capability approval procedure is applicable.

# 11.1 Qualification approval procedure

See the generic specification, clause 3 and 5.1 of the sectional specification.

### 11.2 Capability approval procedure

See IEC 60747-10.

#### 12 Structural similarity procedures

See clause 6 of the sectional specification.

# 13 Test conditions and inspection requirements

#### 13.1 General

The blank detail specification is used to maintain a uniform presentation of tests in the detail specification.

Wherever possible, reference is made to higher-order documents (sectional specification, generic specification). This avoids duplication of text and has the advantage that modifications in the higher-order documents automatically apply to all the blank detail specifications (avoiding the subsequent updating of all blank detail specifications, following a modification in the sectional or generic specifications).

## 13.2 Sampling requirements and formation of inspection lots

For the sampling requirements, the blank detail specification shall make reference to clause 9 of the sectional specification and to 3.7 of the generic specification.

The blank detail specification shall state that, for group A, the choice between the AQL and LTPD systems shall be made in the detail specification.

Regarding the formation of inspection lots, the blank detail specification shall make reference to 5.1.1 of the sectional specification and to 12.2 of IEC QC 901/002

If the procedure for structurally similar devices is to be applied, the blank detail specification shall make reference to clause 6 of the sectional specification and to 8.5.3 of IEC QC 001002.

If for qualification approval it is permitted to use method a) of 11.3.1 of IEC QC 001002, the blank detail specification shall give the sampling requirements (see also clause 9 of the sectional specification).

#### 13.3 Inspection tables

[In the following tables, the values and exact test conditions to be used shall be specified as required for a given type, and as required by the relevant test in the relevant publication. Only those characteristics listed in clause 6 for the given application(s) shall be tested.]

[The choice between alternative tests or test methods shall be made when a detail specification is written.]

[When several devises are included in the same detail specification, the relevant conditions and/or values should be given on successive lines, if possible avoiding repetition of identical conditions and/or values.]

Throughout the following text, reference to a subclause number is made with respect to the generic specification unless otherwise stated, and test methods are quoted from clause 4 of the sectional specification.

GROUP A Lot-by-lot

All tests are non-destructive (see 3.6.6 of the generic specification)

Inspection	Symbol	Reference	Conditions at Tamb		In	specti	on rec	uirem	ent lin	nit	
or test			or $T_{\text{case}} = 25 ^{\circ}\text{C}$ , unless otherwise	Тур	e A	Тур	е В	Тур	e C	Тур	oe D
			specified (see clause 4 of the generic specification)	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.
Sub-group A1											
External visual examination		60747-10 4.2.1.1					^(		0		
Sub-group A2a						_<	(	>	Ď		
Inoperative devices						$ \langle \ \rangle$		\Q\		ļ	
Sub-group A3							MY	X	$\overline{}$		
Power supply current(s)	$I_{xxi}$		See clause 6	×	×	(X)	<b> </b>  &	× ×	×	×	×
Sub-group A4		60747-4, IX, 3	See clause 6		X	70					
Linear gain	$G_{lin}$			( )	<i>{\\\</i>	×				×	
Linear gain flatness	$\Delta G_{lin}$		$\wedge$ $\wedge$ $\rangle$	K	$\times$		×				×
Power gain	$G_{p}$			B.	$\sum_{i=1}^{n} f_i$	×				×	
Power gain flatness	$\Delta G_{p}$		7 / 11/1				×				×
Gain reduction	$\Delta G_{red}$		Call			×					
Limiting output power	P <sub>o(Itg)</sub>		( Colon					×	×		
Limiting output power flatness	$\Delta P_{ m o(ltg)}$	~/ ?	yi&						×		
Output power	$\langle P \rangle$	1				×				×	
Output power at 1 dB-gain compression	P <sub>o((dB)</sub>	/ Cife.		×*		×				×	
Noise figure /	\ \F\\				×						
Magnitude of the input reflection coefficient (input return loss)	JS11)			×		×		×		×	
Magnitude of the output reflection coefficient (output return loss)	1 <b>6</b> 22			×		×					
* Where appropriat	e			·	·			·			

# GROUP B Lot-by-lot

[(in the case of category 1, see 2.6 of the generic specification)]

LSL = lower specification limit USL = upper specification limit

from group A

Only tests marked (D) are destructive (3.6.6)

Inspection	Symbol	Reference	Conditions at $T_{amb}$										
or test			or T <sub>case</sub> = 25 °C, unless otherwise	Тур	oe A	Тур	e B	Тур	e C	Тур	e D		
			specified (see clause 4 of the generic specification)	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
Sub-group B1		60747-10,			^		//	XX	$\bigvee$	•			
Dimensions		4.2.2, and Appendix B					126		>				
Sub-group B3						de l	1, 1	\					
Robustness of terminations where applicable: - Bending (D)		60749, II, 1.2	Force = [see 60749, II 1.2]	No d	mage	\ \ \\		/					
Sub-group B4				X									
Solderability		60749, II, 2.1	[Solder bath preferred]	Good	wettin	g							
Sub-group B8		$\wedge$	(19)										
Electrical endurance		V C	168 h										
with final measurement			reverse bias or operating life	[to be	specif	fied]							
Sub-group CRRL	Attribute infor	mation for B3,	B4 and B8.	•	•			•		•			

# GROUP C Periodic

LSL = lower specification limit USL = upper specification limit

from group A

Only tests marked (D) are destructive (3.6.6)

Inspection	Symbol	Reference	and a second sec										
or test			or T <sub>case</sub> = 25 °C, unless otherwise	Тур	e A	Тур	e B	B Type C		Тур	oe D		
			specified (see clause 4 of the generic specification)	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max		
Sub-group C1		60747-10,				$\wedge$	\	190					
Dimensions		4.2.2 and appendix B			^			XX	$\searrow$	•			
Sub-group C2a		60747-4, IX, 3	See clause 6	_			Mail						
Intermodulation distortion	$P_{\rm n}/P_{\rm 1}$								×		×		
Power at the intercept point	$P_{n(IP)}$			(3)				×		×			
Magnitude of the reverse transmission coefficient (isolation)	S <sub>12</sub>			OX.		×		×		×			
Conversion coefficient of amplitude modulation to phase modulation	α <sub>(AM-PM)</sub>		Jis Hill						×		×		
Group delay time	$t_{d(g_{KP})}$	> / */					×		×		×		
Sub-group C2c		~ 19CH	[note]							•			
Transient energy rating				[to be	specif	fied]							
Sub-group C2d	11-6	14.											
Thermal resistance	Rth(j-c)		[to be specified]						×		×		
Sub-group C3	Phi				•	•	•		•	•	•		
Robustness of terminations where applicable:													
– tensile and/or – torque (D)		60749, II, 1.1 60749, II, 1.4		>> N	o dama	age							

GROUP C - Periodic (continued)

Inspection	Symbol	Reference	Conditions at T <sub>amb</sub>		In	specti	on req	uirem	ent lin	nit	
or test			or T <sub>case</sub> = 25 °C, unless otherwise	Тур	e A	Тур	е В	Тур	e C	Тур	e D
			specified (see clause 4 of the generic specification)	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.
Sub-group C4											
Resistance to soldering heat (D)		60749, II, 2.2	Periodicity = 6 months								
with final measurements				[to be	specif	ied]			0		
Sub-group C5			[note]			^<	(	70	Ď		
Rapid change of temperature:					^	$\langle \ \rangle$		X		•	
a) Cavity packages							1/2/2		>		
Rapid change of temperature followed by:		60749, III, 1.1	10 cycles	$\leq$		106	( )	\			
<ul><li>electrical tests</li></ul>		[see sub- group A2]	[to be selected from A2]	(to be	specif	ied]					
<ul> <li>sealing, fine leak detection</li> </ul>		60749, III, 5.2, 5.3	[to be specified]	\$ / K (		>					
and:				Ø.	٦) ٔ						
<ul> <li>sealing, gross leak detection</li> </ul>		60068-2-17, test Qc	[to be specified]								
b) Non-cavity and epoxy-sealed cavity devices	·		( Sun)								
Rapid change of temperature followed by:		60749, III, 1.1	500 cycles								
<ul><li>external visual examination</li></ul>		60747-10 4.2.(.1	, i								
<ul><li>damp heat, steady state</li></ul>		60749, W. 4A	Severity 3 24 h								
- electrical tests	P. W.	[see sub- group A2]	[to be selected from A2]	[to be	specif	ied]					
Sub-group C6	01/		[note]								_
Acceleration, steady-state [for cavity devices only]		60749, II, 5	[to be specified]								
with final measurements				[to be	specif	ied]					

GROUP C - Periodic (continued)

Inspection	Symbol	Reference	Conditions at T <sub>amb</sub>	••••									
or test			or T <sub>case</sub> = 25 °C, unless otherwise	Ту	ре А	Тур	oe B	Тур	e C	Тур	e D		
			specified (see clause 4 of the generic specification)	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max		
Sub-group C7			[note]										
Damp heat, steady- state (D)													
a) for cavity packages		60749, III, 4A	Severity: 56 days for categories II and III, 21 days for category I			\(			600				
b) for non-cavity and epoxy-sealed cavity packages		60749, III, 4A	Severity 3 for categories II and III, Severity 2 for		\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	/	Jan.	K					
followed by:  – electrical tests		[see sub- group A2]	category I [to be selected from A2]	[to be	spec	fied]		>					
Sub-group C8				K	$\mathcal{I}$	$\nearrow$							
Electrical endurance		see 60748-11, 12.3, 12.4	1 000 h [high-temperature reverse bias or operating life]	[to be	e speci	fiedl							
with final measurement			operating in a	lio De	эресі	ileuj							
Sub-group C9			(i)										
Storage at high temperature (D)	$\langle \rangle$	60749, 111, 2	1 000 h min, at $[T_{\text{sig}}]$ max.]										
with final measurement		Cifer	$\triangleright$	[to be	e speci	fied]							
Sub-group CRRL	Attributes into Measuremen	ormation for Ca information be	, C4, C5 C6, C7 and Cefore and after C8.	C9.									
NOTE After the thi	ee successful	consecutive te	sts, the periodicity ma	y be r	educed	to on	ce per	year.					

# GROUP D Qualification approval tests

When required, these tests shall be prescribed in the detail specification for qualification approval only.

Inspection	Symbol	Reference	Conditions at $T_{amb}$		In	specti	ion rec	uirem	ent lin	nit	
or test			or T <sub>case</sub> = 25 °C, unless otherwise	Type A		Type B		Type C		Тур	e D
			specified (see clause 4 of the generic specification)	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.
Sub-group D8									0	ı	
Electrical endurance (D)		60748-11, 12.3, 12.4	Category I: not applicable Category II: 2 000 h Category III: 3 000 h [note 1]	[to be	special	lied)	Jan			•	
with final measurement			Conditions: [note 2]	$\bigcirc$		Z,	$\rangle$	•			

NOTE 1 The endurance duration shown is the accumulated time for Group and Group D endurance.

NOTE 2 The conditions under which endurance tests are carried out shall be determined as follows:

the choice of power dissipation, operating temperature and supply voltage shall be made in the following order of precedence:

- a) the mean power dissipation in each functionally accessible section of the circuit shall be the maximum permitted by the detail specification;
- b) the ambient temperature shall be the maximum permitted by the detail specification at the power dissipation of a);
- c) the supply voltages shall be the maximum permitted by the detail specification unless limited by a) or b).

# 13.4 Delayed delivery

See 3.6.7 of IEC 60747-10, unless otherwise specified.

# 14 Additional measurement method

See 4.3.1.1 of the generic specification.